

FHX04LG, 05LG, 06LG

Super Low Noise HEMT

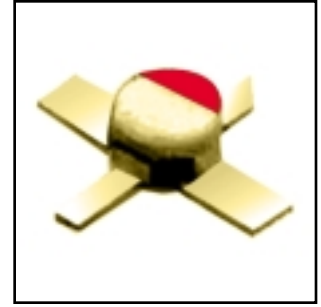
FEATURES

- Low Noise Figure: 0.75dB (Typ.)@f=12GHz (FHX04)
- High Associated Gain: 10.5dB (Typ.)@f=12GHz
- $L_g \leq 0.25\mu\text{m}$, $W_g = 200\mu\text{m}$
- Gold Gate Metallization for High Reliability
- Cost Effective Ceramic Microstrip (SMT) Package
- Tape and Reel Packaging Available

DESCRIPTION

The FHX04LG, FHX05LG, FHX06LG is a High Electron Mobility Transistor(HEMT) intended for general purpose, low noise and high gain amplifiers in the 2-18GHz frequency range. The devices are packaged in cost effective, low parasitic, hermetically sealed metal-ceramic package for high volume telecommunication, TVRO, VSAT or other low noise applications.

Fujitsu's stringent Quality Assurance Program assures the highest reliability and consistent performance.



ABSOLUTE MAXIMUM RATING (Ambient Temperature Ta=25°C)

Item	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	3.5	V
Gate-Source Voltage	V_{GS}	-3.0	V
Total Power Dissipation	P_t^*	180	mW
Storage Temperature	T_{stg}	-65 to +175	°C
Channel Temperature	T_{ch}	175	°C

*Note: Mounted on Al_2O_3 board (30 x 30 x 0.65mm)

Fujitsu recommends the following conditions for the reliable operation of GaAs FETs:

1. The drain-source operating voltage (V_{DS}) should not exceed 2 volts.
2. The forward and reverse gate currents should not exceed 0.2 and -0.05 mA respectively with gate resistance of 4000Ω.
3. The operating channel temperature (T_{ch}) should not exceed 80°C.

ELECTRICAL CHARACTERISTICS (Ambient Temperature Ta=25°C)

Item		Symbol	Condition	Limit			Unit
				Min.	Typ.	Max.	
Saturated Drain Current		I _{DSS}	V _{DS} = 2V, V _{GS} = 0V	15	30	60	mA
Transconductance		g _m	V _{DS} = 2V, I _{DS} =10mA	35	45	-	mS
Pinch-off Voltage		V _p	V _{DS} = 2V, I _{DS} =1mA	-0.2	-0.7	-1.5	V
Gate Source Breakdown Voltage		V _{GSO}	I _{GS} = -10μA	-3.0	-	-	V
Noise Figure	FHX04LG	NF	V _{DS} = 2V, I _{DS} = 10mA, f = 12GHz	-	0.75	0.85	dB
Associated Gain		G _{as}		9.5	10.5	-	dB
Noise Figure	FHX05LG	NF		-	0.9	1.1	dB
Associated Gain		G _{as}		9.5	10.5	-	dB
Noise Figure	FHX06LG	NF		-	1.1	1.35	dB
Associated Gain		G _{as}		9.5	10.5	-	dB
Thermal Resistance		R _{th}	Channel to Case	-	300	400	°C/W

AVAILABLE CASE STYLES: LG

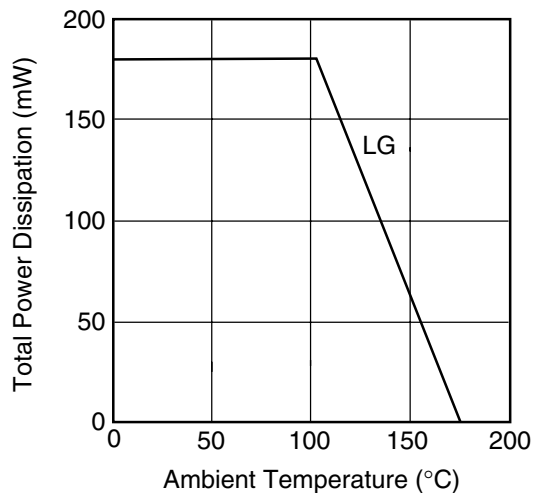
Note: RF parameters are measured on a sample basis as follows:

Lot qty.		Sample qty.	Accept/Reject
1200	or less	125	(0,1)
1201	to 3200	200	(0,1)
3201	to 10000	315	(1,2)
10001	or over	500	(1,2)

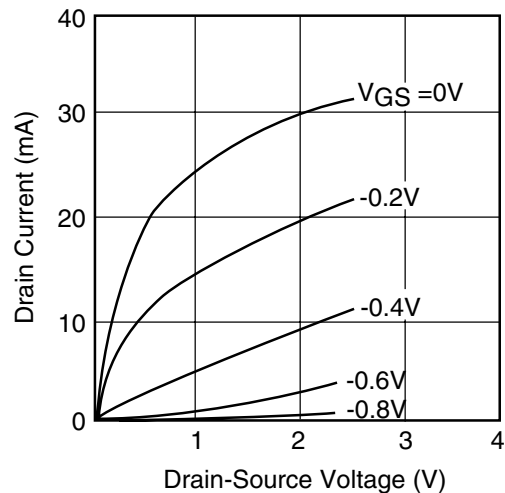
FHX04LG, 05LG, 06LG

Super Low Noise HEMT

POWER DERATING CURVE

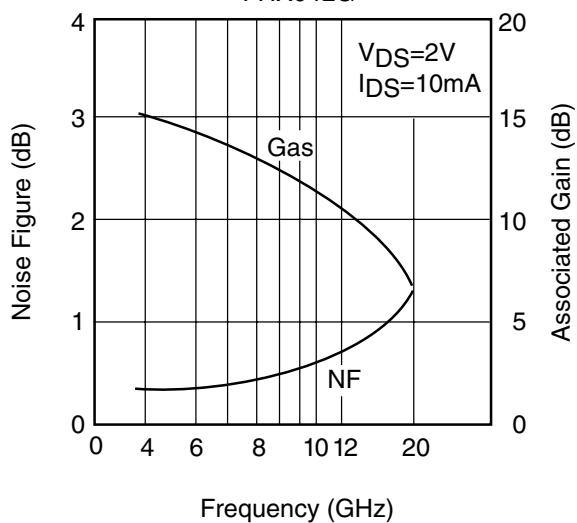


DRAIN CURRENT vs. DRAIN-SOURCE VOLTAGE



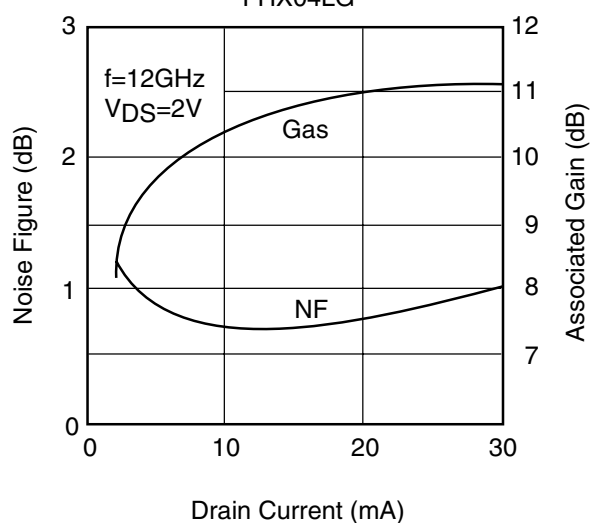
NF & Gas vs. FREQUENCY

FHX04LG



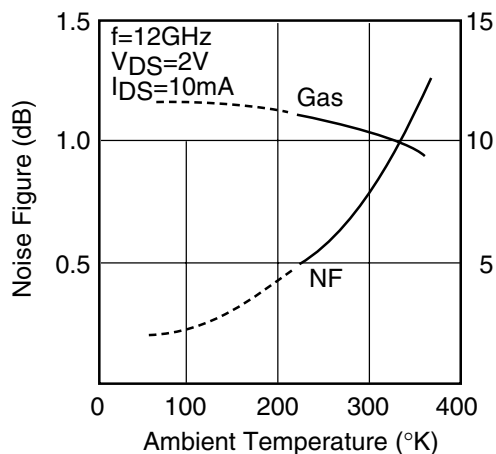
NF & Gas vs. I_{DS}

FHX04LG

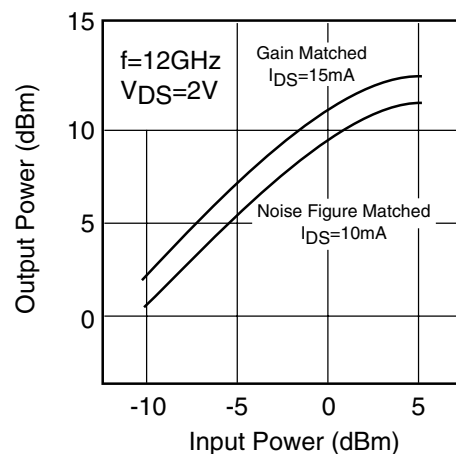


NF & Gas vs. TEMPERATURE

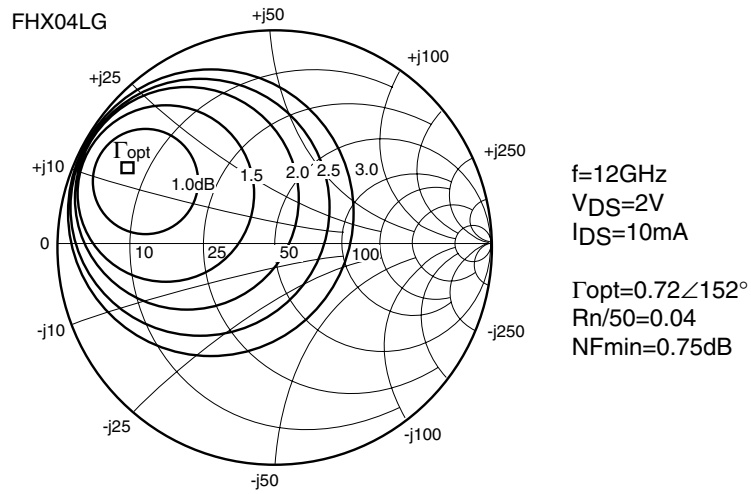
FHX04LG



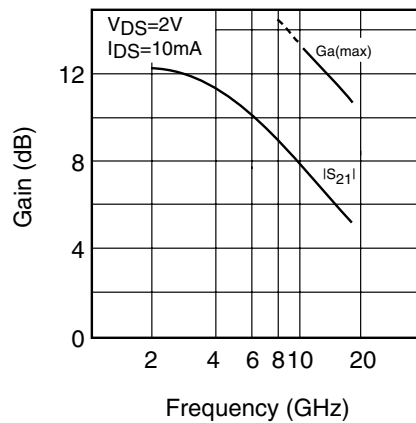
OUTPUT POWER vs. INPUT POWER



TYPICAL NOISE FIGURE CIRCLE



Ga(max) AND $|S_{21}|$ vs. FREQUENCY FHX04LG



NOISE PARAMETERS

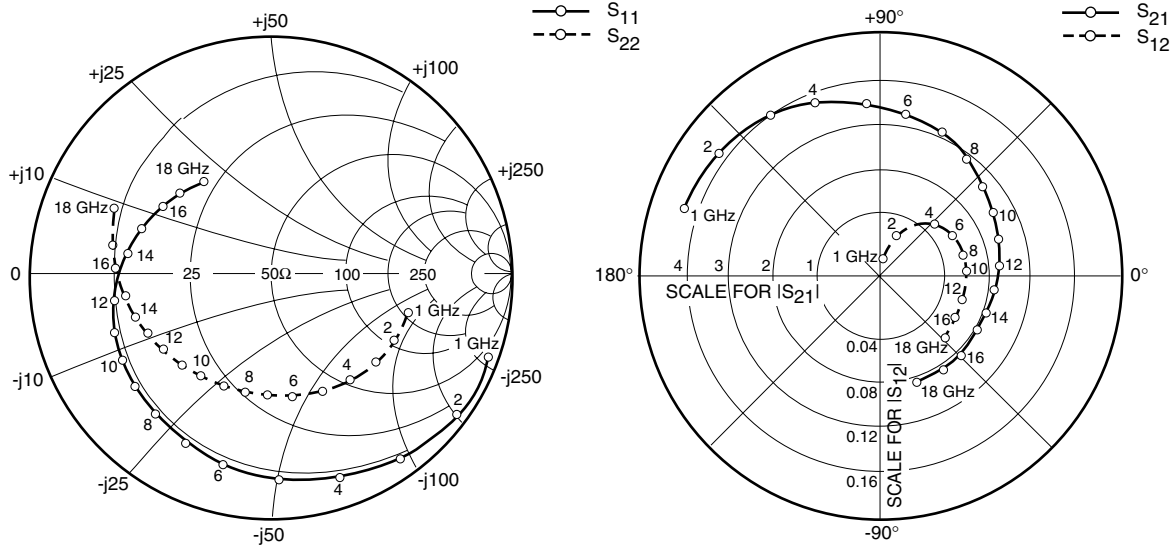
FHX04LG

$V_{DS}=2\text{V}$, $I_{DS}=10\text{mA}$

Freq. (GHz)	Γ_{opt}		NFmin (dB)	Rn/50
	(MAG)	(ANG)		
2.0	0.99	29.0	0.33	0.43
4.0	0.97	53.0	0.35	0.30
6.0	0.93	77.0	0.45	0.20
8.0	0.87	101.0	0.55	0.12
10.0	0.80	127.0	0.66	0.07
12.0	0.72	152.0	0.75	0.04
14.0	0.63	178.0	0.88	0.03
16.0	0.53	-156.0	1.05	0.05
18.0	0.42	-129.0	1.30	0.09

FHX04LG, 05LG, 06LG

Super Low Noise HEMT



S-PARAMETERS

FHX04LG

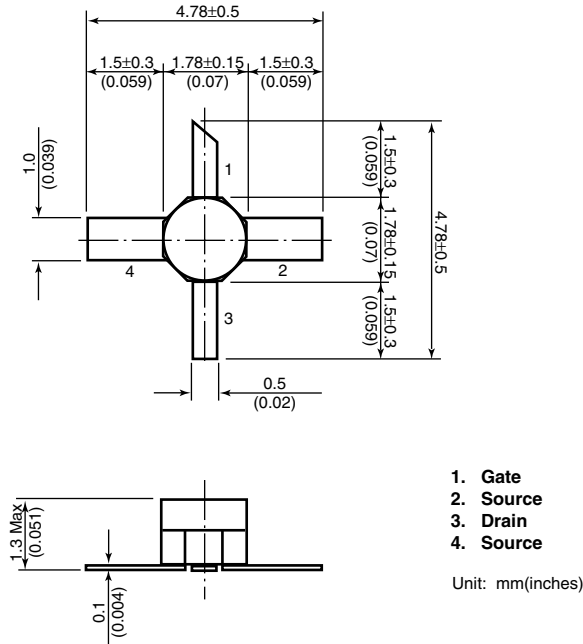
$V_{DS} = 2V$, $I_{DS} = 10mA$

FREQUENCY (GHZ)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
1.0	0.990	-19.3	4.232	162.1	0.016	75.1	0.576	-14.3
2.0	0.965	-37.5	4.115	144.1	0.030	64.8	0.563	-28.1
3.0	0.928	-55.2	3.923	127.4	0.042	53.3	0.546	-41.2
4.0	0.886	-72.1	3.737	110.9	0.052	41.9	0.525	-54.4
5.0	0.844	-88.3	3.518	95.6	0.059	32.2	0.505	-67.6
6.0	0.804	-103.4	3.302	80.8	0.063	23.9	0.489	-80.7
7.0	0.771	-117.4	3.090	66.4	0.066	16.6	0.484	-93.0
8.0	0.741	-129.6	2.876	53.1	0.065	11.5	0.487	-104.5
9.0	0.717	-140.3	2.703	40.7	0.066	4.9	0.497	-115.1
10.0	0.695	-150.8	2.592	28.6	0.065	-0.3	0.503	-124.9
11.0	0.675	-161.2	2.476	16.4	0.064	-3.0	0.517	-135.7
12.0	0.650	-171.5	2.374	4.2	0.064	-6.4	0.534	-145.8
13.0	0.630	178.9	2.277	-7.8	0.063	-9.3	0.552	-156.1
14.0	0.607	170.2	2.176	-19.1	0.064	-12.5	0.585	-164.6
15.0	0.585	161.8	2.144	-30.7	0.065	-16.4	0.617	-171.7
16.0	0.557	151.8	2.151	-43.2	0.066	-22.2	0.642	177.8
17.0	0.522	140.9	2.142	-56.9	0.067	-29.4	0.673	169.5
18.0	0.480	128.4	2.136	-71.2	0.068	-39.2	0.694	159.7

FHX04LG, 05LG, 06LG

Super Low Noise HEMT

Case Style "LG" Metal-Ceramic Hermetic Package



For further information please contact:

FUJITSU COMPOUND SEMICONDUCTOR, INC.

2355 Zanker Rd.

San Jose, CA 95131-1138, U.S.A.

Phone: (408) 232-9500

FAX: (408) 428-9111

www.fcsi.fujitsu.com

FUJITSU MICROELECTRONICS EUROPE, GmbH

Quantum Devices Division

Network House

Norreys Drive

Maidenhead, Berkshire SL6 4FJ

Phone: +44 (0)1628 504800

FAX: +44 (0)1628 504888

CAUTION

Fujitsu Compound Semiconductor Products contain **gallium arsenide (GaAs)** which can be hazardous to the human body and the environment. For safety, observe the following procedures:

- Do not put these products into the mouth.
- Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.
- Observe government laws and company regulations when discarding this product. This product must be discarded in accordance with methods specified by applicable hazardous waste procedures.

Fujitsu Limited reserves the right to change products and specifications without notice.
The information does not convey any license under rights of Fujitsu Limited or others.

© 1998 FUJITSU COMPOUND SEMICONDUCTOR, INC.

Printed in U.S.A. FCSI0598M200

FUJITSU

Компания «Life Electronics» занимается поставками электронных компонентов импортного и отечественного производства от производителей и со складов крупных дистрибьюторов Европы, Америки и Азии.

С конца 2013 года компания активно расширяет линейку поставок компонентов по направлению коаксиальный кабель, кварцевые генераторы и конденсаторы (керамические, пленочные, электролитические), за счёт заключения дистрибьюторских договоров

Мы предлагаем:

- Конкурентоспособные цены и скидки постоянным клиентам.
- Специальные условия для постоянных клиентов.
- Подбор аналогов.
- Поставку компонентов в любых объемах, удовлетворяющих вашим потребностям.
- Приемлемые сроки поставки, возможна ускоренная поставка.
- Доставку товара в любую точку России и стран СНГ.
- Комплексную поставку.
- Работу по проектам и поставку образцов.
- Формирование склада под заказчика.
- Сертификаты соответствия на поставляемую продукцию (по желанию клиента).
- Тестирование поставляемой продукции.
- Поставку компонентов, требующих военную и космическую приемку.
- Входной контроль качества.
- Наличие сертификата ISO.

В составе нашей компании организован Конструкторский отдел, призванный помогать разработчикам, и инженерам.

Конструкторский отдел помогает осуществить:

- Регистрацию проекта у производителя компонентов.
- Техническую поддержку проекта.
- Защиту от снятия компонента с производства.
- Оценку стоимости проекта по компонентам.
- Изготовление тестовой платы монтаж и пусконаладочные работы.



Тел: +7 (812) 336 43 04 (многоканальный)

Email: org@lifeelectronics.ru

www.lifeelectronics.ru